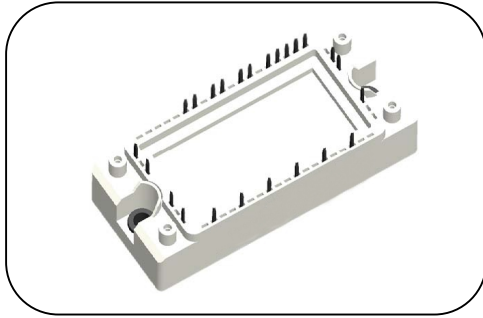


**Features:**

- 10us short circuit capability
- Low switching losses
- VCE(sat) with Positive temperature coefficient
- Fast & soft reverse recovery anti-parallel FWD

Typical Applications:

- Inverter for motor drive(VFD)
- AC and DC servo drive amplifier
- Uninterruptible power supply

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		VALUE			UNIT
				Min	Type	Max	
V _{CES}	Collector-Emitter voltage	T _J =25 C				1200	V
V _{GES}	Gate-Emitter voltage	T _J =25 C				±20	V
I _C	Collector current	Continuous@ T _C =125 C				25	A
I _{CP}		T _P =1ms				50	A
T _J	Junction temperature	/				150	℃
T _{op}	Operating temperature	/		-40		125	℃
T _{stg}	Storage temperature	/		-40		125	℃
V _{iso}	Isolation between terminal and copper base	T _J =25 C , AC: 1minute		2500			V
I _{CES}	Zero gate voltage collector current	T _J =25 C ,V _{CE} =1200V, V _{GE} =0V				0.1	mA
I _{GES}	Gate-Emitter leakage current	T _J =25 C ,V _{CE} =0V, V _{GE} =±20V		-0.4		0.4	μA
BV _{CES}		V _{GE} =0V, I _C =4mA		1200			V
V _{GE(th)}	Gate-Emitter threshold voltage	T _J =25 C ,V _{CE} =20V, I _C =1.0mA		5.0	5.8	6.5	V
V _{CE(sat)}	Collector-Emitter saturation voltage	T _J =25 C ,V _{GE} =15V, I _C =25A			1.7	2.15	V
R _{Gint}	Integrated gate resistor				8		Ω
Q _g	Gate Charge	T _J =25 C ,V _{CE} =600V,I _C =25A,V _{GE} =15V			0.24		μC
C _{ies}	Input capacitance	T _J =25 C ,V _{CE} =25V, V _{GE} =0V, f=1MHz			1.80		nF
C _{oes}	output capacitance				1.65		nF
C _{res}	Reverse transfer capacitance				0.064		nF
t _{(d)on}	Turn-on time	V _{CC} =600V, I _C =25A, V _{GE} =±15V, R _g =36Ω, Inductive load	T _J =25 C		90		ns
			T _J =125 C		90		ns
T _J =25 C				30		ns	
T _J =125 C				50		ns	
t _{(d)off}	Turn-off time		T _J =25 C		420		ns
			T _J =125 C		520		ns
T _J =25 C				70		ns	
T _J =125 C				90		ns	
t _f							
t _{sc}	Short circuit withstand time	V _{CES} ≤600V, V _{GE} = ±15V			10		μs
V _F	Forward on voltage	T _J =25 C ,I _F =40A			1.65	2.15	V
		T _J =125 C ,I _F =40A			1.65		V
I _{FRM}	Repetitive peak forward current				50		A
t _{rr}	Reverse recovery time	T _J =25 C ,I _F =25A, di _F /dt=-1600A/ μ s, V _R =600V			290		ns
R _{th(j-c)}	Thermal resistance(per chip)	IGBT			0.8		℃/W
		FWD			1.35		℃/W
R ₂₅	Resistance	T _{Vj} =25℃			5		kΩ

B25/50	$R_2 = R_{25} \exp [B25/50(1/T_2 - 1/(298,15K))]$		3375		K
Outline	256H5P2				

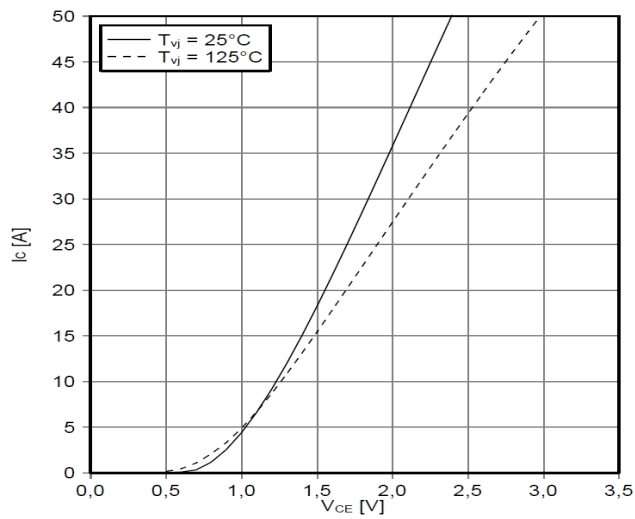


Fig.1 output characteristic IGBT, Inverter

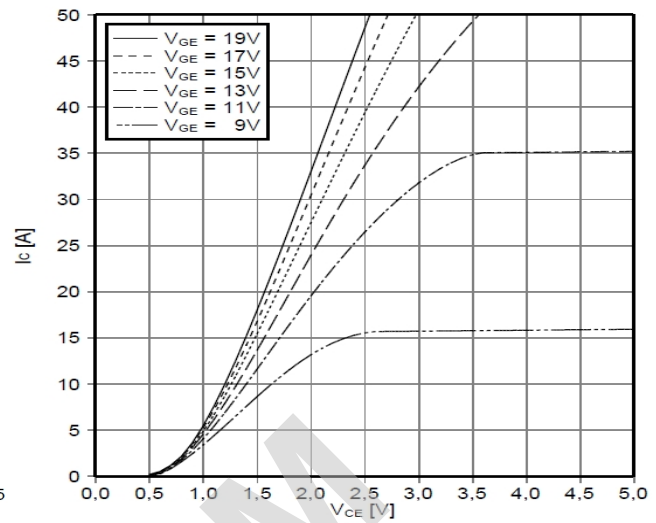


Fig.2 output characteristic IGBT, Inverter

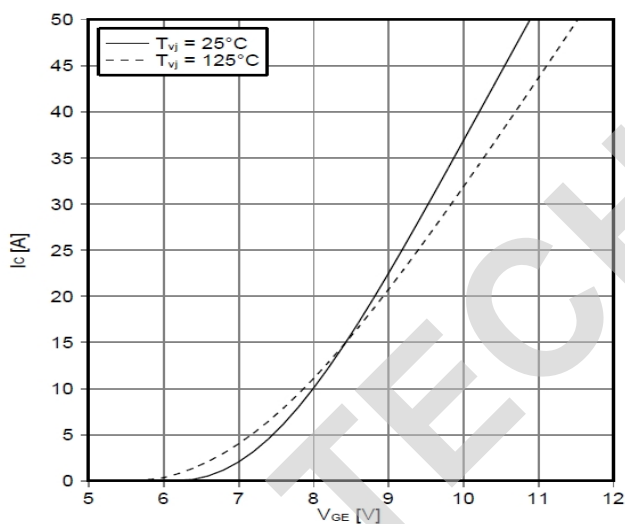


Fig.3 transfer characteristic IGBT, Inverter

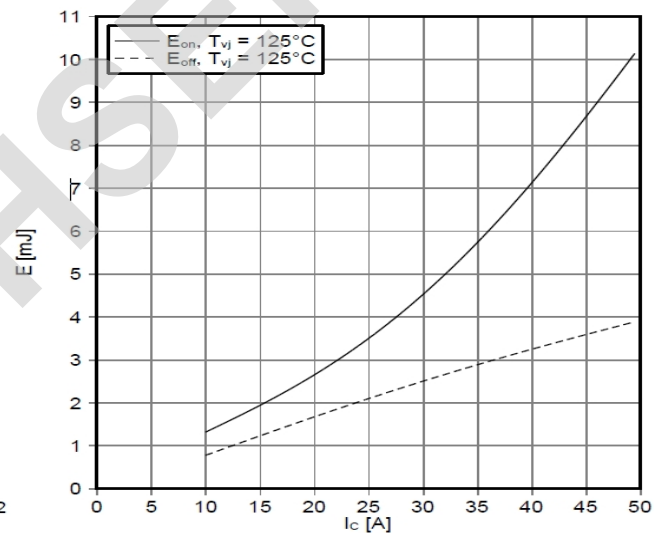


Fig.4 switching losses IGBT, Inverter

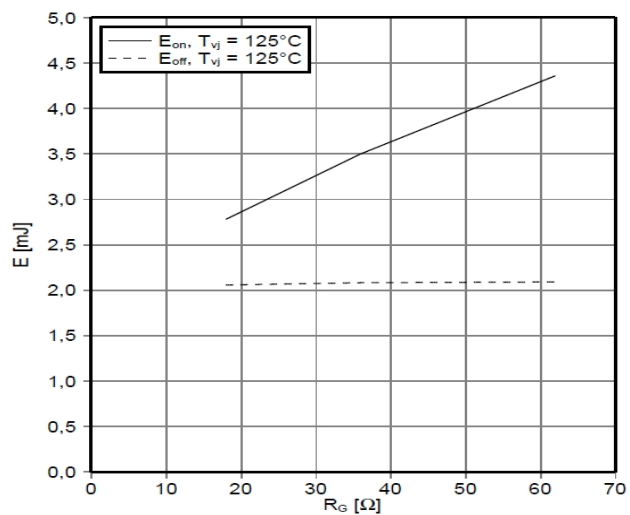


Fig.5 switching losses IGBT, Inverter

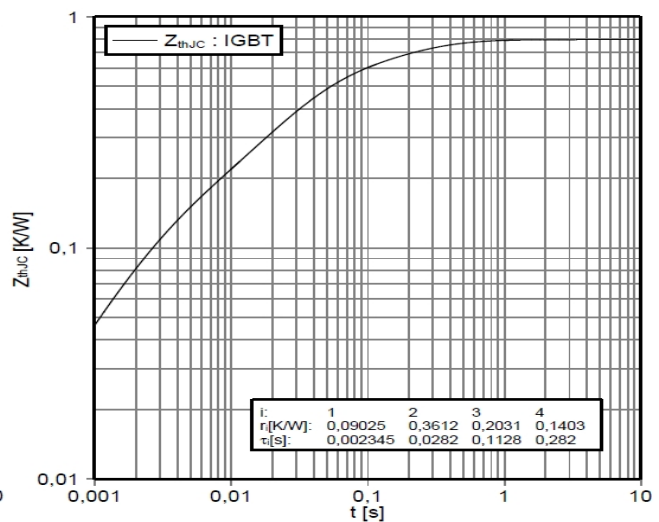


Fig.6 transient thermal impedance IGBT, Inverter

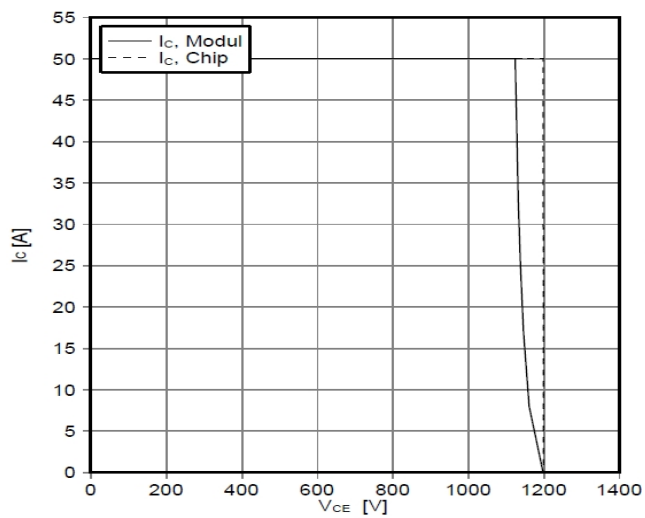


Fig.7 reverse bias safe operating area IGBT, Inverter (RBSOA)

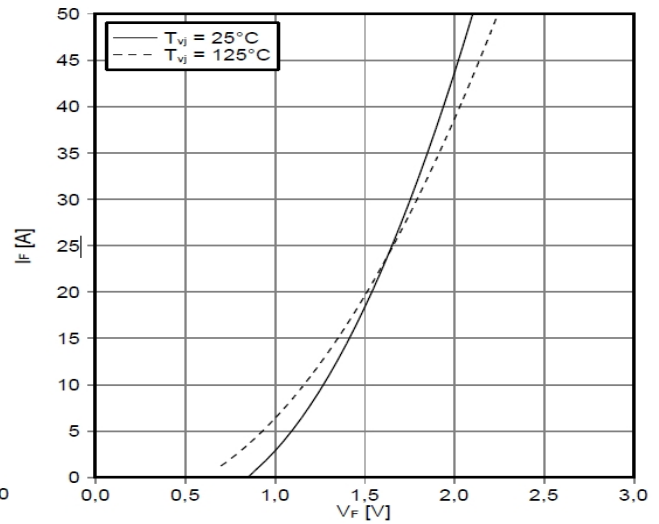


Fig.8 forward characteristic of Diode, Inverter

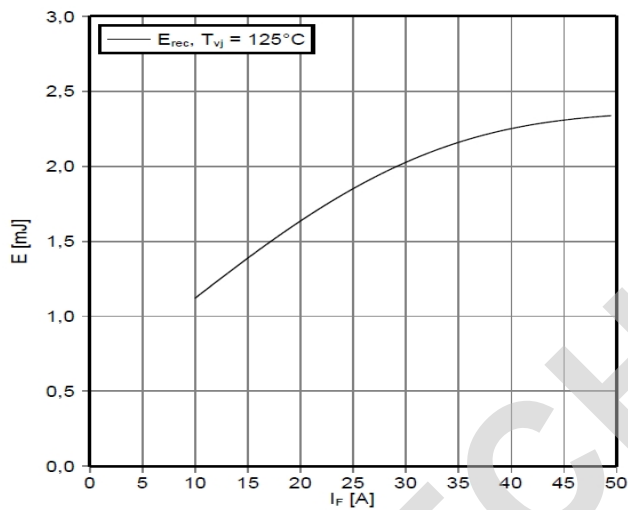


Fig.9 switching losses Diode, Inverter

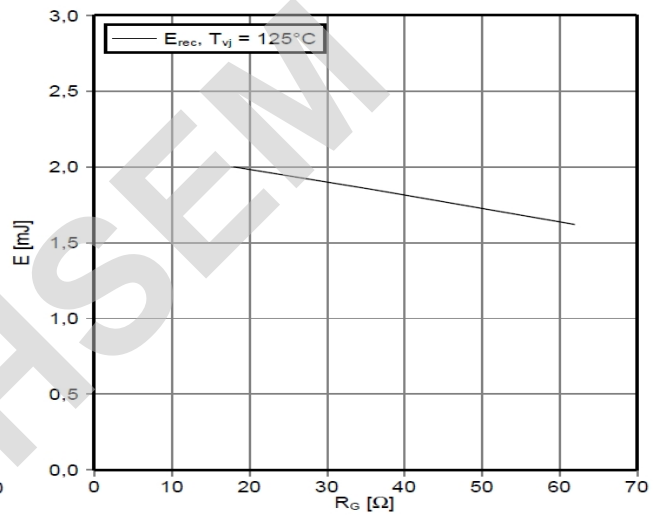


Fig.10 switching losses Diode, Inverter

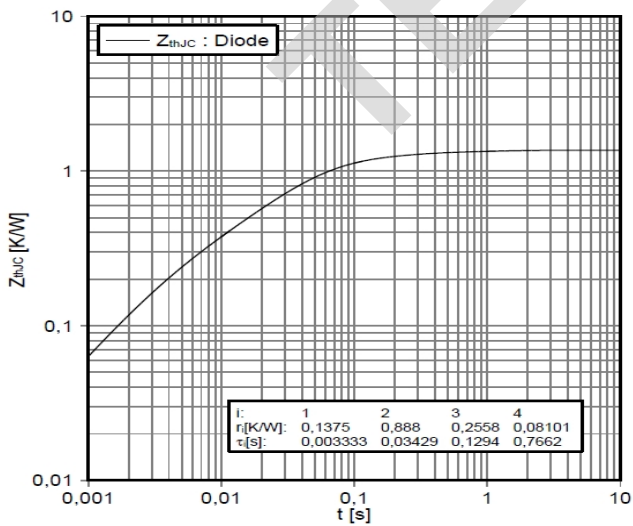


Fig.11 transient thermal impedance Diode, Inverter

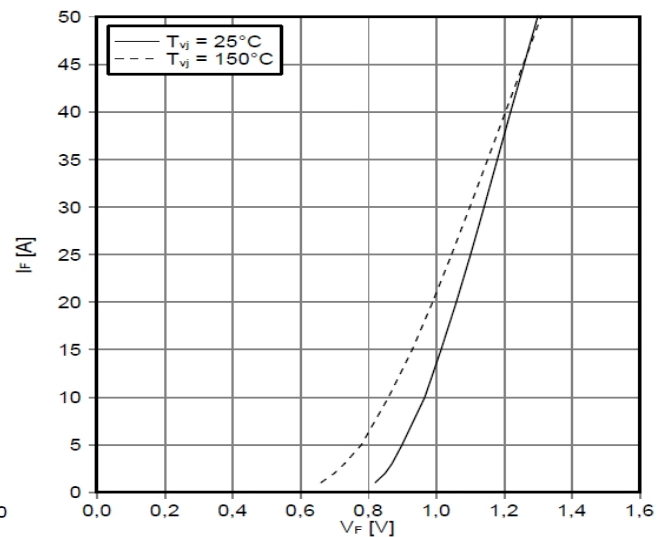


Fig.12 forward characteristic of Diode, Rectifier

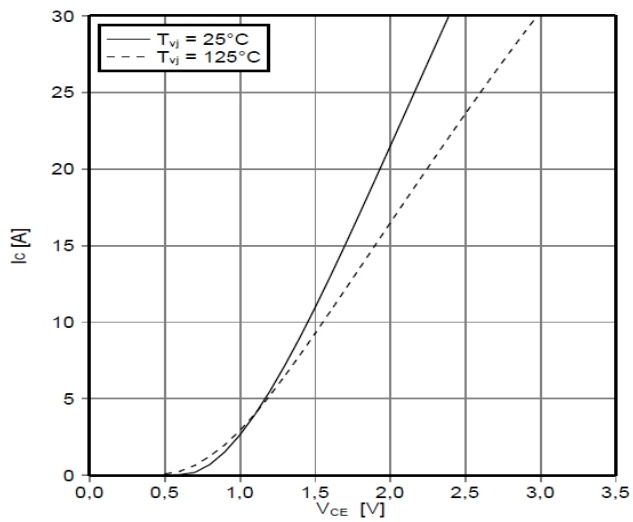


Fig.13 output characteristic IGBT, Brake-Chopper

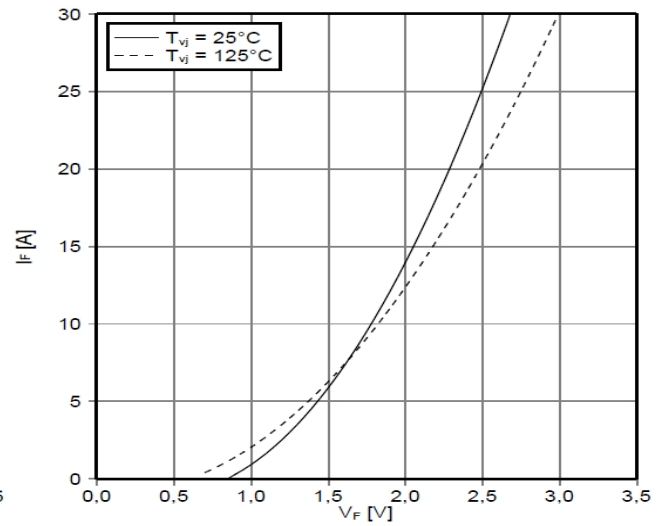


Fig.14 forward characteristic of Diode, Brake-Chopper

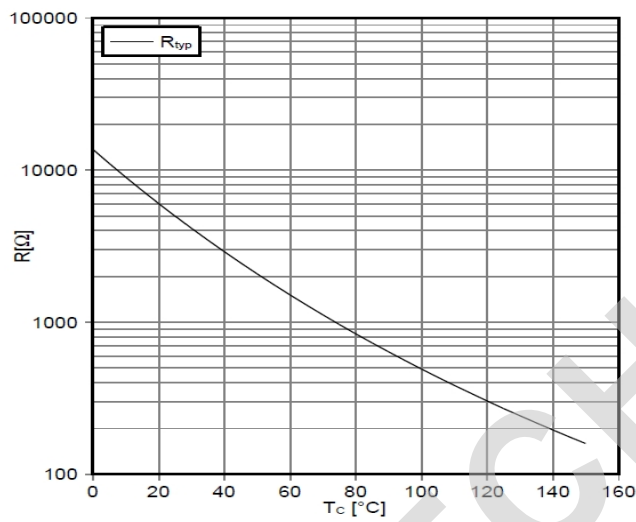


Fig.15 NTC-Thermistor-temperature characteristic

